

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

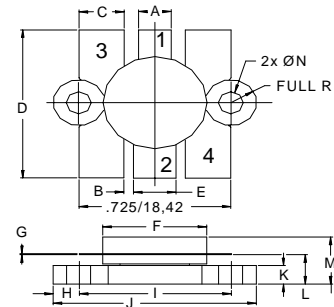
The **ASI MRF317** is Designed for Class C, 28 V High Band Applications up to 200 MHz.

FEATURES:

- Internal Input Matching Network
- $P_G = 9.0$ dB at 100 W/150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	20 A
V_{CBO}	65 V
V_{CEO}	36 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	270 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.65 °C/W

PACKAGE STYLE .500 6L FLG


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

1 = Collector 2 = Base 3&4 = Emitter

CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 100$ mA	65			V
BV_{CES}	$I_C = 100$ mA	65			V
BV_{CEO}	$I_C = 100$ mA	35			
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			5.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 5.0$ A	10		80	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz			250	pF
P_G η_c	$V_{CE} = 28$ V $P_{OUT} = 100$ W $f = 150$ MHz	9.0	60		dB %